

Technical Data

TRANSISTOR

maximum ratings

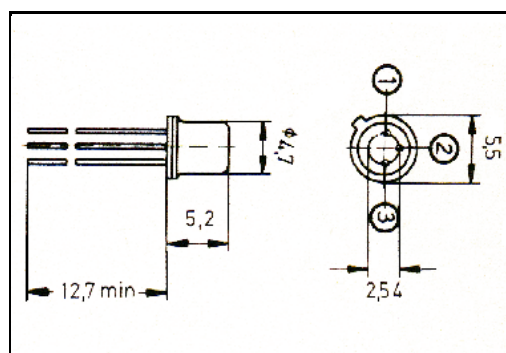
Voltage, Collector to Base (VCBO)	60.0	V	NO.	2N2907A-M
Voltage, Collector to Emitter (VCE)	60.0	V	TYPE	PNP
Voltage, Emitter to Base (VEBO)	5.0	V		
Collector Current (IC)	0.6	A		
Base Current (IB)	0.2	A	CASE	TO-18
Max. Power Dissipation (PT) at TC = 25 °C	1.2	W		MIL-S-19500
Max. Thermal Resistance (Rth J-C)	146.0	°C/W		BURN-IN 48h/125°C
Max. Junction Temperature (TJ)	200.0	°C		

PERFORMANCE CHARACTERISTICS at $T_c = 25^\circ\text{C}$, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	BVCEO	IC = 10 mA (1)	60.0	-	V
2.	BVCBO	IC = 10 μ A	60.0	-	V
3.	BVEBO	IE = 10 μ A	5.0	-	V
4.	ICBO	VCB = 50 V	-	10.0	nA
5.	-	VCB = 50 V , TA = 150 °C	-	10.0	μ A
6.	hFE	IC = 0.1 A , VCE = 10 V (1)	100.0	-	-
7.	-	IC = 1 mA , VCE = 10 V (1)	100.0	-	-
8.	-	IC = 10 mA , VCE = 10 V (1)	100.0	-	-
9.	-	IC = 150 mA , VCE = 10 V (1)	100.0	300.0	-
10.	-	IC = 50 mA , VCE = 10 V (1)	50.0	-	-
11.	VCE(SAT)	IC = 150 mA , IB = 15 mA (1)	-	0.4	V
12.	-	IC = 500 mA , IB = 50 mA (1)	-	1.6	V
13.	VBE(SAT)	IC = 150 mA , IB = 15 mA (1)	-	1.3	V
14.	-	IC = 500 mA , IB = 50 mA (1)	-	2.6	V
15.	fT	IC = 20 mA , VCE = 20 V , f = 100 MHz	200.0	-	MHz
16.	Cobo	VCB = 10 V	-	8.0	pF
17.	Cebo	VEB = 2 V	-	30.0	pF
18.					
19.					
20.					

Notes (1)pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

DIMENSIONS
in mm



Marking 2N2907A-M + GREEN DOT

Customer GENERAL PURPOSE